



#### 100V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

# **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
100V	62mΩ @ V <sub>GS</sub> = 10V	20A
	$77m\Omega$ @ $V_{GS} = 6V$	16A

## **Description**

This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

## **Applications**

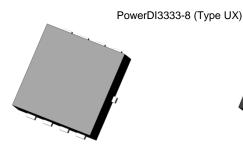
- **Power Management Functions**
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.

#### **Features and Benefits**

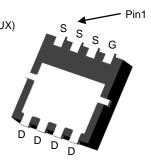
- Low R<sub>DS(ON)</sub> Ensures On State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher **Density End Products**
- Occupies just 33% of the Board Area Occupied by SO-8 **Enabling Smaller End Product**
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

#### **Mechanical Data**

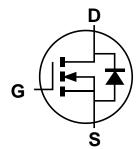
- Case: PowerDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)







**Bottom View** 



**Equivalent Circuit** 

#### Ordering Information (Note 4)

Part Number	Case	Quantity per Reel
DMT10H072LFV-7	PowerDI3333-8 (Type UX)	2,000/Tape & Reel
DMT10H072LFV-13	PowerDI3333-8 (Type UX)	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

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4. For packaging details, go to our website athttps://www.diodes.com/design/support/packaging/diodes-packaging/

# **Marking Information**



T72= Product Type Marking Code YYWW = Date Code Marking  $\overline{YY}$  = Last Two Digits of Year (ex: 19 = 2019) WW = Week Code (01 to 53)



# **Maximum Ratings** (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V <sub>DSS</sub>	100	V	
Gate-Source Voltage	V <sub>GSS</sub>	±20	V	
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 5)	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	4.7 3.7	А
Continuous Drain Current V <sub>GS</sub> = 10V (Note 6)	$T_C = +25$ °C $T_C = +70$ °C	I <sub>D</sub>	20 16	А
Pulsed Drain Current (10µs Pulse, T <sub>C</sub> =+25°C, Package Limited)	I <sub>DM</sub>	80	Α	
Pulsed Body Diode Current (10µs Pulse, T <sub>C</sub> =+25°C, Package Limite	I <sub>SM</sub>	80	Α	
Maximum Body Diode Continuous Current	Is	2	Α	
Avalanche Current (Note 9), L=0.1mH	I <sub>AS</sub>	6	Α	
Avalanche Energy (Note 9), L=0.1mH	E <sub>AS</sub>	1.8	mJ	

#### Thermal Characteristics (@TA = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	2	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ heta JA}$	61	°C/W
Total Power Dissipation (Note 6)	P <sub>D</sub>	37.8	W
Thermal Resistance, Junction to Case (Note 6)	$R_{ heta JC}$	3.3	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

#### **Electrical Characteristics** (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	1 23		- 71-				
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	-	-	1	μΑ	V <sub>DS</sub> = 80V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	$V_{GS(TH)}$	1.5	-	2.8	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
		-	50.6	62	mΩ	$V_{GS} = 10V, I_D = 4.5A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	-	61.2	77	11122	$V_{GS} = 6V, I_{D} = 4A$	
	R <sub>DS(ON)</sub>	-	82.5	109	mΩ	$V_{GS} = 4.5V, I_D = 2.7A$	
Diode Forward Voltage	$V_{SD}$	-	0.76	1	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	-	228	-	рF	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V, f = 1MHz	
Output Capacitance	Coss	-	89.3	-	pF		
Reverse Transfer Capacitance	$C_{rss}$	-	2.5	-	pF		
Gate Resistance	Rg	-	8.2	-	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	-	2.5	-	nC	V <sub>DS</sub> = 50V, I <sub>D</sub> = 4.5A	
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	-	4.5	-	nC		
Gate-Source Charge	Q <sub>gs</sub>	-	0.6	-	nC		
Gate-Drain Charge	Q <sub>qd</sub>	-	1.3	-	nC		
Turn-On Delay Time	t <sub>D(ON)</sub>	-	3.0	-	ns		
Turn-On Rise Time	t <sub>R</sub>	-	3.1	-	ns	$V_{DS} = 50V, R_L = 11\Omega$ $V_{GS} = 10V, R_{GEN} = 3\Omega$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	-	12.3	-	ns		
Turn-Off Fall Time	t <sub>F</sub>	-	4.3	-	ns		
Reverse Recovery Time	t <sub>RR</sub>	-	22.9	-	ns	I <sub>F</sub> = 4.5A, di/dt = 300A/μs	
Reverse Recovery Charge	Q <sub>RR</sub>	-	45.2	-	nC		

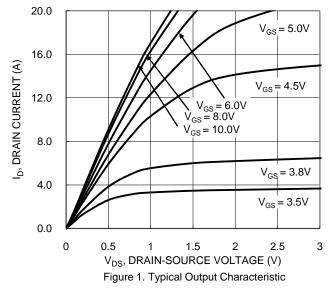
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

<sup>6.</sup> Thermal resistance from junction to soldering point (on the exposed drain pad).

<sup>7.</sup> Short duration pulse test used to minimize self-heating effect.

<sup>8.</sup> Guaranteed by design. Not subject to product testing. 9.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J = +25^{\circ}C$ .





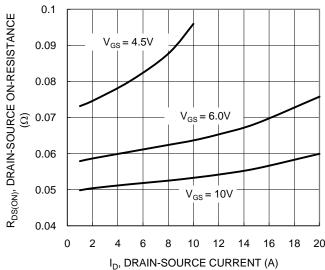


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

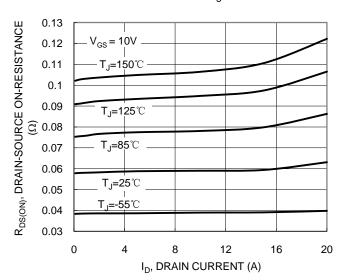


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

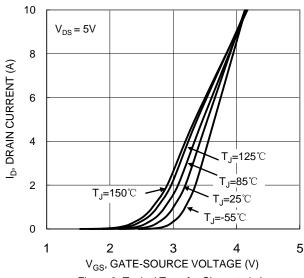


Figure 2. Typical Transfer Characteristic

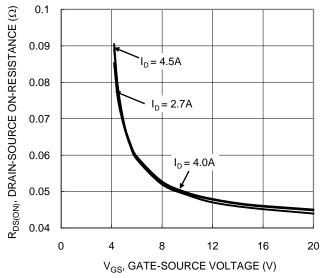


Figure 4. Typical Transfer Characteristic

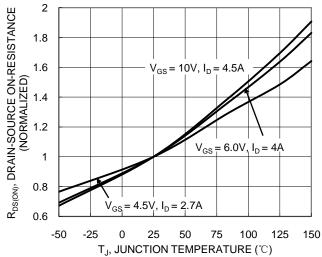


Figure 6. On-Resistance Variation with Junction Temperature





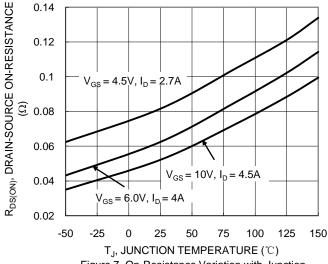


Figure 7. On-Resistance Variation with Junction Temperature

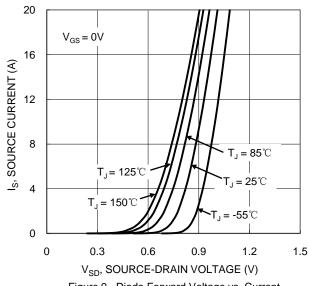
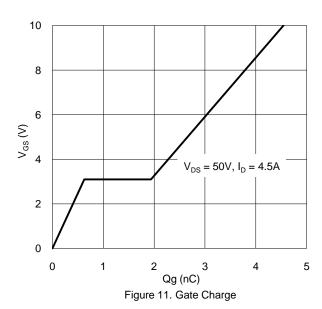
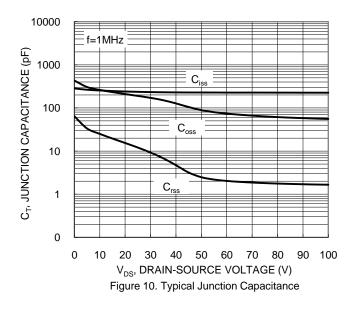


Figure 9. Diode Forward Voltage vs. Current



2.6  $V_{GS(TH)}$ , GATE THRESHOLD VOLTAGE (V) 2.4  $I_D = 1mA$ 2.2 2 1.8  $I_D = 250 \mu A$ 1.6 1.4 1.2 1 -50 -25 0 25 50 75 100 125 150  $T_J$ , JUNCTION TEMPERATURE (°C)

Figure 8. Gate Threshold Variation vs. Junction Temperature



100  $R_{DS(ON)}$  Limited DRAIN CURRENT (A) 10 =100μs P<sub>W</sub> =1ms J<sub>(Max)</sub> = 150°C  $T_C = 25^{\circ}C$  $P_W = 10 \text{ms}$ Single Pulse  $P_W = 100 ms$ DUT on Infinite DC Heatsink  $V_{GS} = 10V$ 0.1 0.1 1000 V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



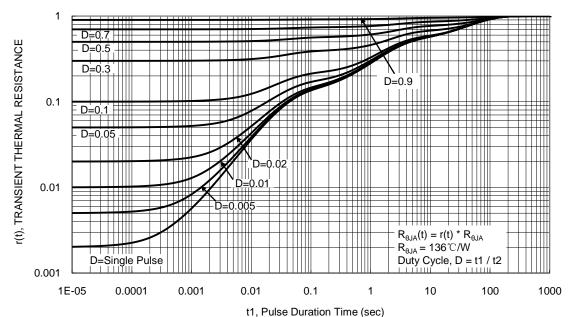


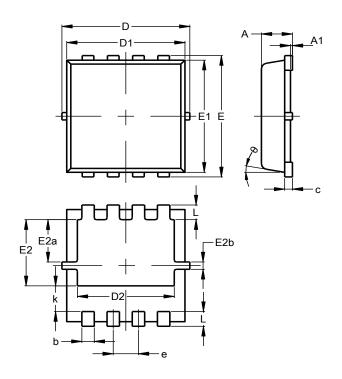
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8 (Type UX)

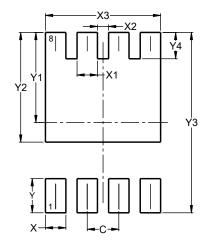


PowerDI3333-8 (Type UX)					
Dim	Min	Мах Тур			
Α	0.75	0.85	0.80		
A1	0.00	0.05	-		
b	0.25	0.40	0.32		
С	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	2.30	2.70	2.50		
Е	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E2a	0.95	1.35	1.15		
E2b	0.10	0.30	0.20		
е	0.65 BSC				
k	0.50	0.90	0.70		
٦	0.30	0.50	0.40		
θ	0°	12°	10°		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8 (Type UX)



Dimensions	Value (in mm)		
С	0.650		
X	0.420		
X1	0.420		
X2	0.230		
Х3	2.370		
Υ	0.700		
Y1	1.850		
Y2	2.250		
Y3	3.700		
Y4	0.540		



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